SHARP S12MD1V/S12MD3

S12MD1V/S12MD3

Photothyristor Coupler

* Lead forming type (I type) and taping reel type (P type) of \$12MD1V are also available. (\$12MD1VI/\$12MDIP)

■ Features

- 1. High RMS ON-state current (I_{T} : MAX. $200\text{mA}_{\text{rms}}$)
- 2. High repetitive peak OFF-state voltage (V_{DRM} : MIN. 400V)
- 3. Trigger current I $_{FT}$: MAX. 15mA at R $_{G}$ = $20k\Omega$
- 4. For half-wave control ••• \$12MD1V For full-wave control ••• \$12MD3
- 5. Recognized by UL, file No. E64380
- $\ \, \ \, \mbox{\bf $S12MD1V}$ and $\mbox{\bf $S12MD3}$ are for 100V line

■ Applications

- 1. ON-OFF operation for a low power load
- 2. For triggering high power thyristor and

■ Outline Dimensions (Unit: mm) S12MD1V Internal connection diagram 2.54^{±0.25} 16<u>1</u>5<u>4</u>4 S12MD1V SHARP +0+213 1 2 ① Anode 0.9±0.2 2 Cathode3 NC4 Cathode 1.2^{±0.3} $7.12^{\pm0.5}$ $7.62^{\pm0.3}$ S Anode $3.5^{\pm0.5}$ 6 Gate 0.5TYP. $0.5^{\pm0.1}$ $0.26^{\pm0.1}$ θ : 0 to 13° S12MD3 $0.8^{\pm\,0.2}$ Internal connection diagram .8. 7. 6. **76** (5) S12MD3 Anode 12 13 14 W 10 2 3 ①④ Anode 1.2^{±0.3} 0.85[±]0.3 23 Cathode 58 Gate $9.22^{\pm0.5}$ $7.62^{\pm\,0.3}$ 67 Anode/ cathode 0.26^{±0.1}

SHARP S12MD1V/S12MD3

■ Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

	•				
Parameter		Ch - 1	Rating		TT '
		Symbol	S12MD1V	S12MD3	Unit
Input	Forward current	I_F	50		mA
	Reverse voltage	V _R	6		V
	RMS ON-state current	I_{T}	200		mA _{rms}
0	*1 Peak one cycle surge current	I _{surge}	2		A
Output	*2 Repetitive peak OFF-state voltage	V_{DRM}	400		V
	*2 Repetitive peak reverse voltage	V _{RRM}	400	-	V
*3 Isolation voltage		V _{iso}	5 000	1 500	V _{rms}
Operating temperature		T opr	- 30 to + 100		°C
Storage temperature		T _{stg}	- 40 to + 125		°C
*4 Soldering temperature		T _{sol}	260		°C

^{*1 50}Hz, sine wave

■ Electro-optical Characteristics

 $(Ta = 25^{\circ}C)$

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage	V_F	$I_F = 30 mA$	-	1.2	1.4	V
	Reverse current	I_R	$V_R = 3V$	-	-	10-5	A
Output	Repetitive peak OFF-state current	I _{DRM}	$V_{DRM} = Rated, R_G = 20k\Omega$	-	-	10-6	A
	*5Repetitive peak reverse current	I _{RRM}	$V_{RRM} = Rated, R_G = 20k\Omega$	-	-	10-6	A
	ON-state voltage	V _T	$I_T = 200 mA$	-	1.0	1.4	V
	Holding current	I _H	$V_D = 6V$, $R_G = 20k\Omega$	-	0.3	1	mA
	Critical rate of rise of OFF-state voltage	dV/dt	$V_{DRM} = 1/\sqrt{2}$ Rated, $R_G = 20k\Omega$	3	-	-	V/µs
Transfer- charac- teristics	Minimum trigger current	IFT	$V_{\text{D}}\!=6V,R_{\text{L}}\!=100\Omega$, $R_{\text{G}}\!=20k\Omega$	-	-	15	mA
	Isolation resistance	R _{ISO}	DC500V, 40 to 60% RH	5 x 10 ¹⁰	1011	-	Ω
	Turn-on time	t on	$V_D = 6V, I_F = 30mA, R_G = 20k\Omega$, $R_L = 100\Omega$	-	10	60	μs

^{*5} Applies only to **S12MD1V**

Fig. 1 RMS ON-state Current vs.
Ambient Temperature

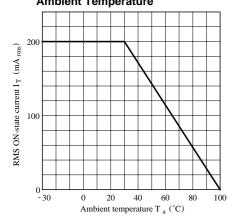
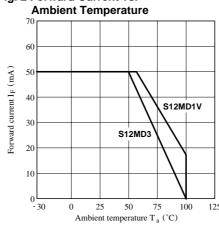


Fig. 2 Forward Current vs.



^{*3 40} to 60% RH, AC for 1 minute

Fig. 3 Forward Current vs. Forward Voltage

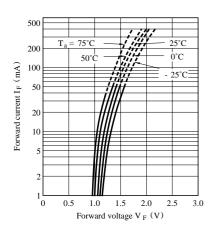


Fig. 5 Minimum Trigger Current vs.
Gate Resistance

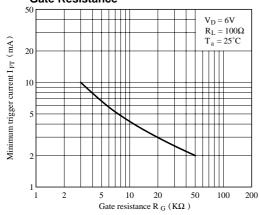


Fig. 7 Critical Rate of Rise of OFF-state Voltage vs. Ambient Temperature

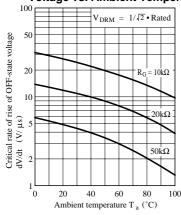


Fig. 4 Minimum Trigger Current vs.
Ambient Temperature

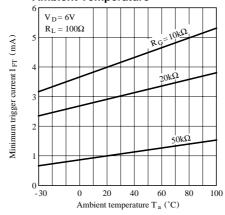


Fig. 6 Break Over Voltage vs. Ambient Temperature

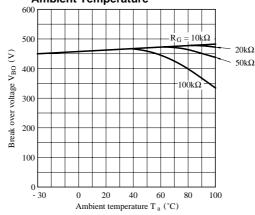


Fig. 8 Holding Current vs.
Ambient Temperature

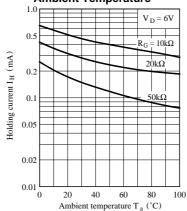
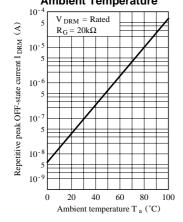


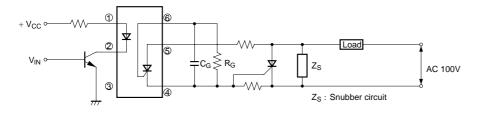
Fig. 9 Repetitive Peak OFF-state Current vs. Ambient Temperature



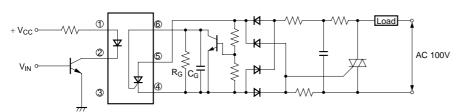
■ Basic Operation Circuit

● S12MD1V

Medium/High Power Thyristor Drive Circuit



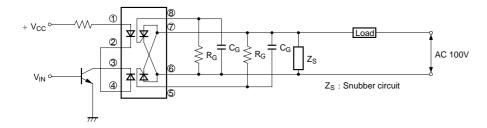
Medium/High Power Triac Drive Circuit (Zero-cross Operation)



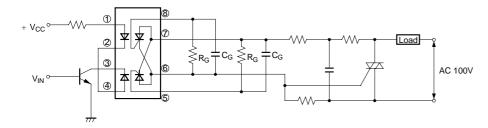
SHARP S12MD1V/S12MD3

● S12MD3

Low Power Load Drive Circuit



Medium/High Power Triac Drive Circuit



• Please refer to the chapter "Precautions for Use" (Page 78 to 93).

Application Circuits

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- Test and measurement equipment
- Industrial control
- Audio visual equipment
- Consumer electronics
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